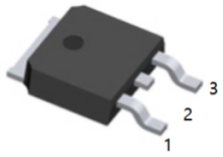
IRFR5305

-60 V P-Channel Enhancement Mode MOSFET

DESCRIPTION

The IRFR5305TR uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge .This device is suitable for use as a load switch or in PWM applications.

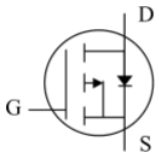


1.G 2.D 3.S

TO-252(DPAK) top view

GENERAL FEATURES

- V_{DS} =- 60V,I_D =-30A
- $R_{DS(ON)}$ < 40mΩ @ V_{GS}=-10V
- $R_{DS(ON)}$ < 55mΩ @ V_{GS}=-4.5V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package



Application

- PWM applications
- Load switch
- Power management

ABSOLUTE MAXIMUM RATINGS(T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-60	V
Gate-Source Voltage	VGS	±20	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D(25℃)	-30	A
	I_D(70℃)	-20	A
	IDM	-60	A
Maximum Power Dissipation	P_D	60	W
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	℃
Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	25	℃/W

ELECTRICAL CHARACTERISTICS (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-48V,V_{GS}=0V			-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.1	-2	-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-20A		31	40	mΩ
		V_{GS}=-4.5V, I_D=-20A		42	55	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-20A	5			S
Input Capacitance	C_{lss}	V_{DS}=-30V,V_{GS}=0V, F=1.0MHz		3060		PF
Output Capacitance	C_{oss}			300		PF
Reverse Transfer Capacitance	C_{rss}			205		PF
Turn-on Delay Time	$t_{d(on)}$	V_{DS}=-30V,V_{GS}=-10V,R_{GEN}=3Ω I_D=1A		14		nS
Turn-on Rise Time	t_r			20		nS
Turn-Off Delay Time	$t_{d(off)}$			40		nS
Turn-Off Fall Time	t_f			19		nS
Total Gate Charge	Q_g	V_{DS}=-30V,I_D=-20A,V_{GS}=-10V		48		nC
Gate-Source Charge	Q_{gs}			11		nC
Gate-Drain Charge	Q_{gd}			10		nC
Body Diode Reverse Recovery Time	T_{rr}	I_F=-20A, dI/dt=100A/μs		40		nS
Body Diode Reverse Recovery Charge	Q_{rr}			56		nC
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-1A		-0.72	-1	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in^2 FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%. **4.** Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

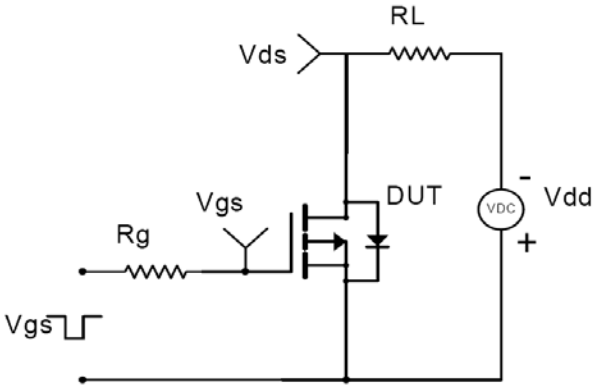


Figure 1:Switching Test Circuit

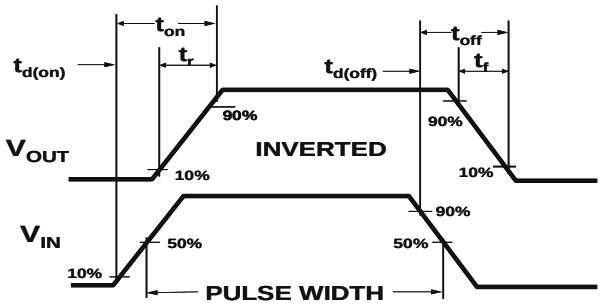


Figure 2:Switching Waveforms

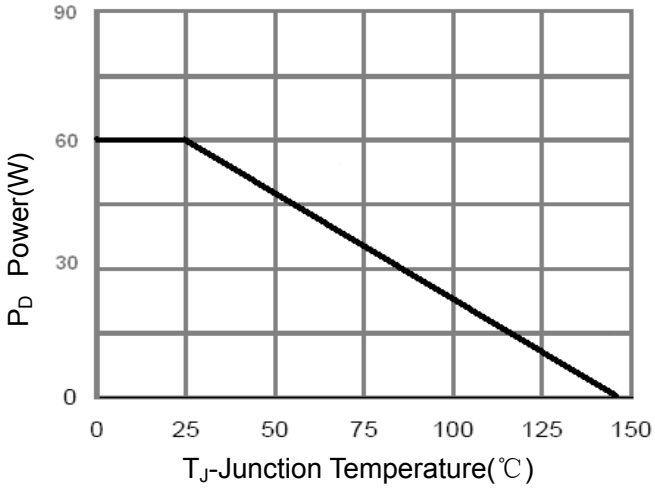


Figure 3 Power Dissipation

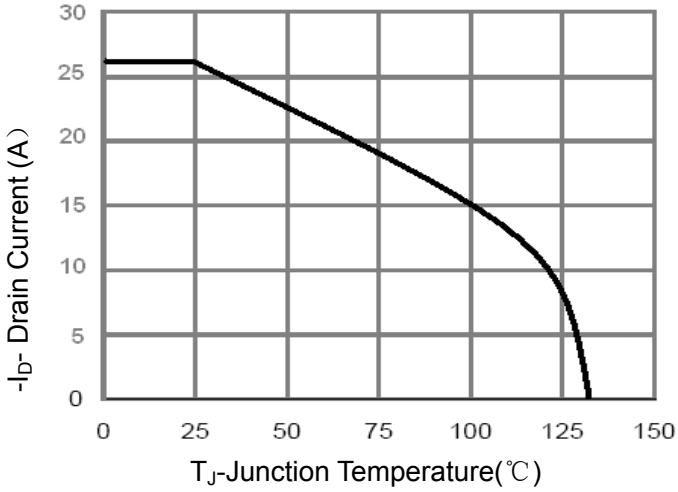


Figure 4 Drain Current

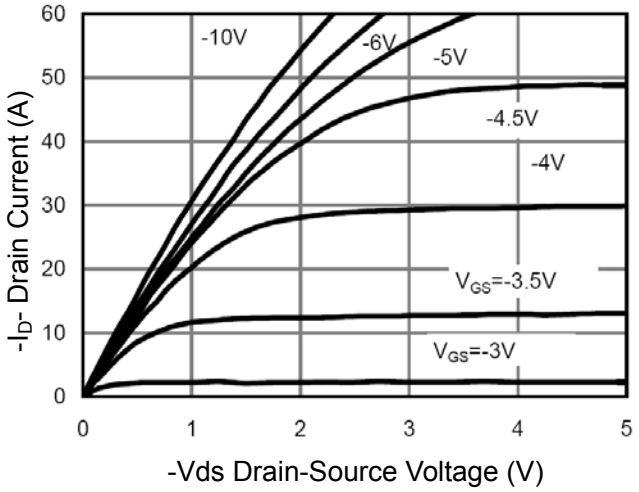


Figure 5 Output CHARACTERISTICS

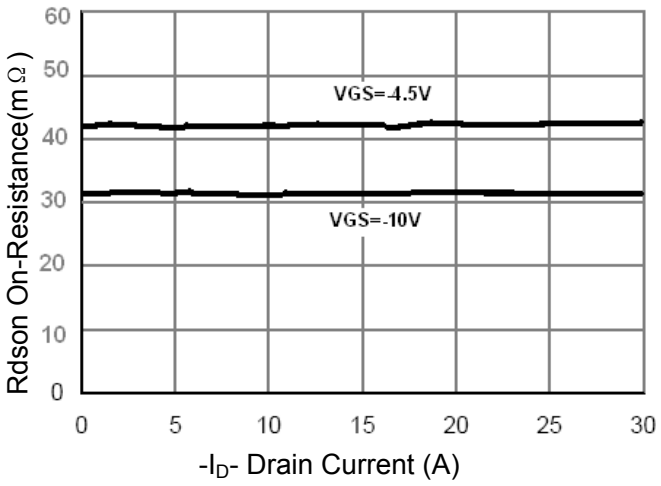


Figure 6 Drain-Source On-Resistance

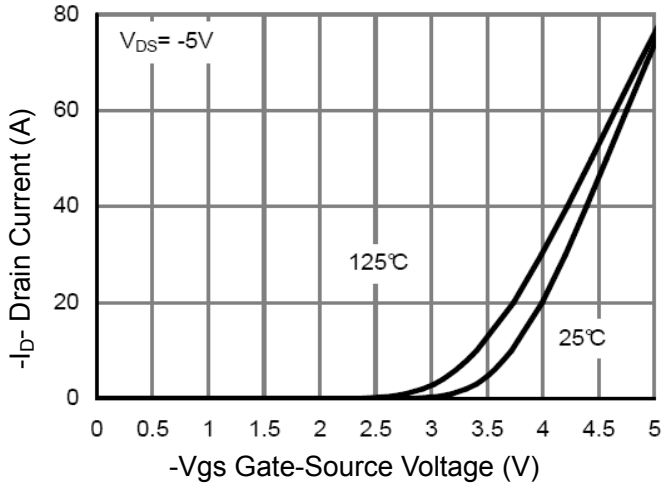


Figure 7 Transfer Characteristics

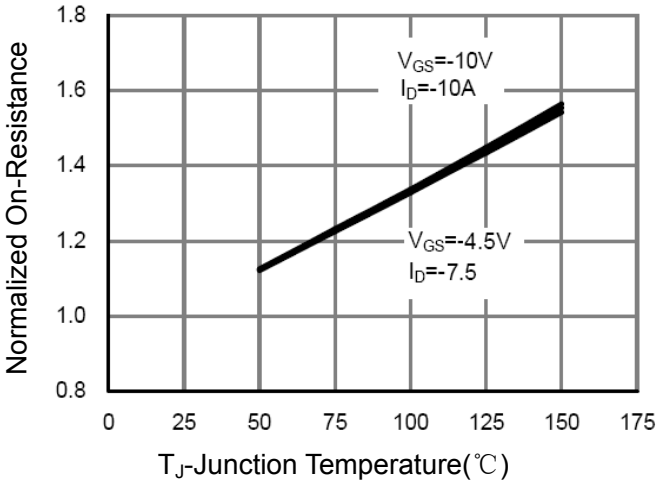


Figure 8 Drain-Source On-Resistance

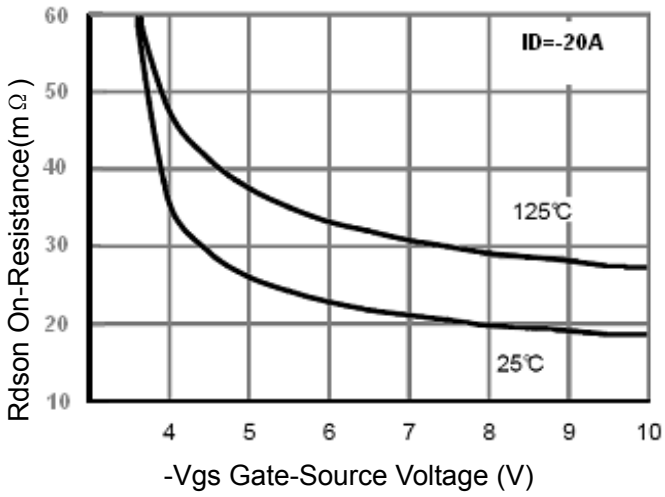


Figure 9 Rdson vs Vgs

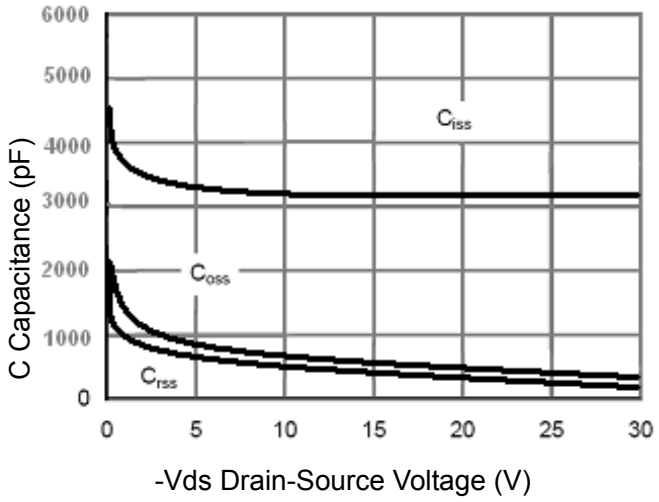


Figure 10 Capacitance vs Vds

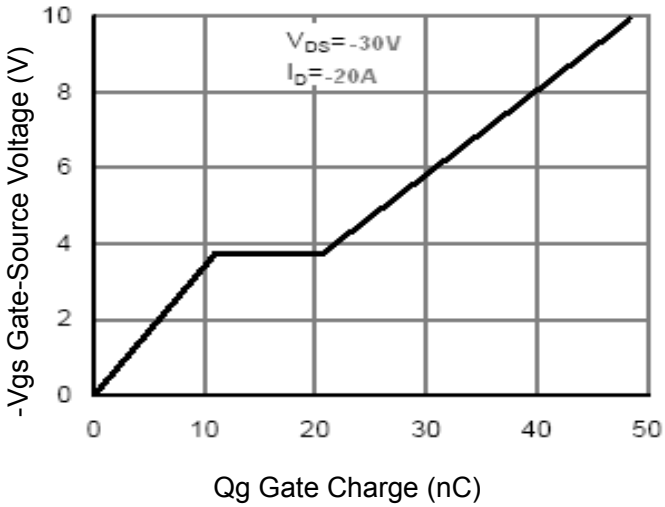


Figure 11 Gate Charge

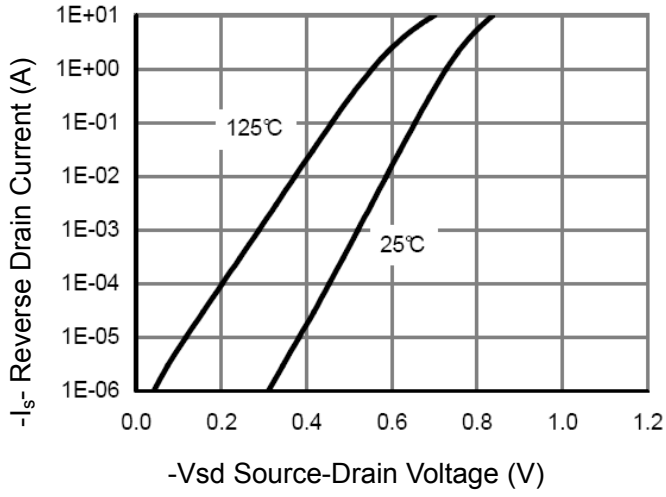


Figure 12 Source- Drain Diode Forward

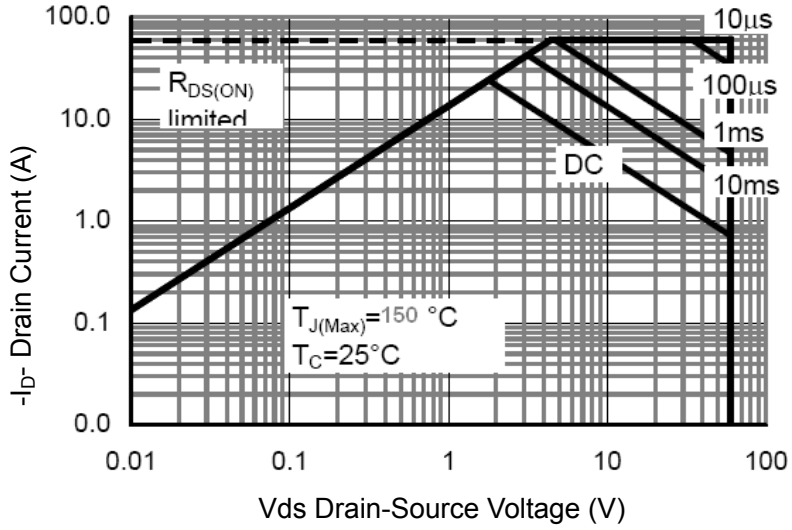


Figure 13 Safe Operation Area

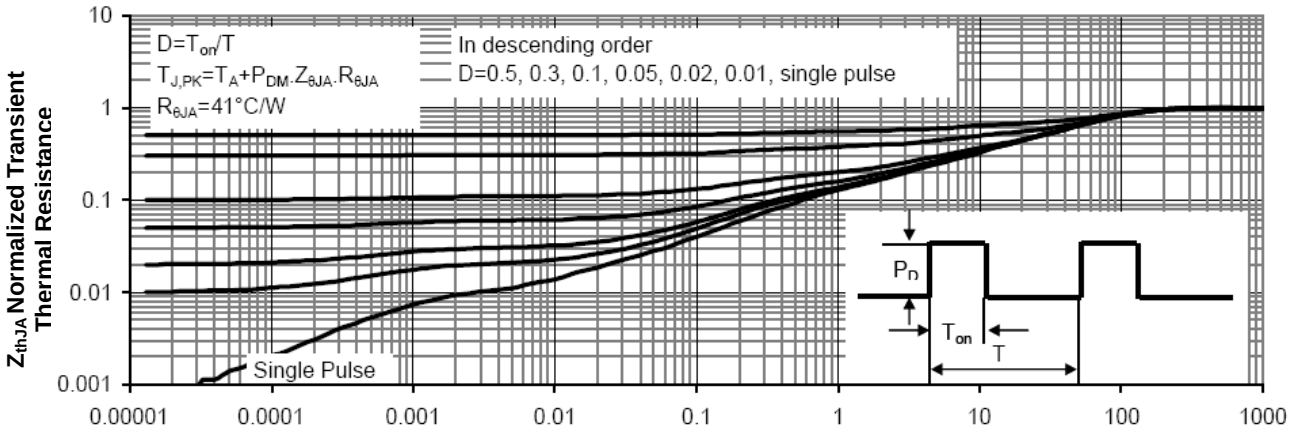
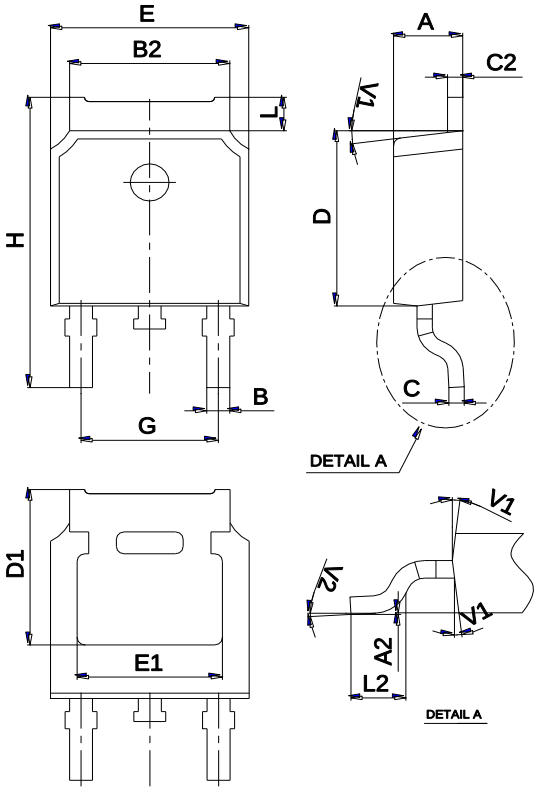


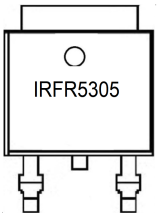
Figure 14 Normalized Maximum Transient Thermal Impedance

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
IRFR5305TR	TO-252	2500	Tape and reel